

MSB55N03N3

30V N-Channel Logic Level Enhancement Mode MOSFET

Features

- VDS=30V
- RDS(ON)=55mΩ@VGS=10V, ID=3.5A
- RDS(ON)=85mΩ@VGS=4.5V, ID=2A
- Lower gate charge
- RoHS compliant package

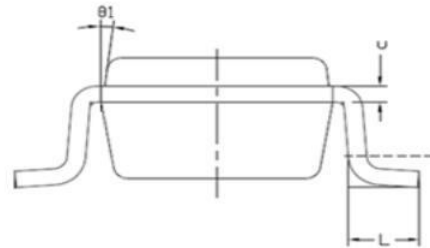
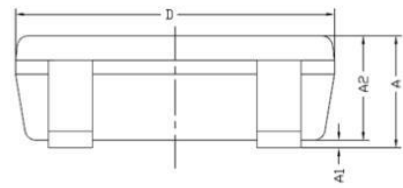
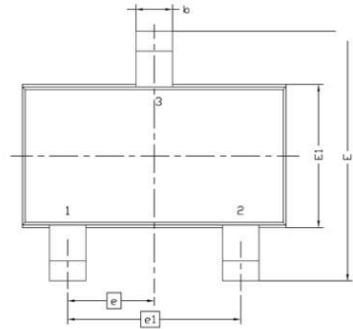
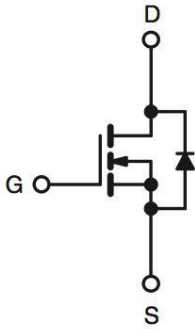
Packing & Order Information

3,000/Reel



**RoHS
COMPLIANT**

Graphic symbol



Symbol	MILLIMETERS	
	MIN	MAX
A	0.8	1.2
A1	0	0.1
A2	0.7	1.1
b	0.3	0.5
c	0.1	0.2
D	2.7	3.1
E	2.6	3
E1	1.4	1.8
e	0.95 BSC	
e1	1.9 BSC	
L	0.3	0.6
θ1	7° NOM	

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

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Absolute Maximum Ratings (Ta=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current -Continuous (T _A =25°C)	3.5	A
	Drain Current -Continuous (T _A =70°C)	2.4	A
I _{DM}	Pulsed Drain Current	14 (Note 1&2)	A
P _D	Total Power Dissipation (T _A =25°C)	1.5 (Note 3)	W
	Total Power Dissipation (T _A =70°C)	1 (Note 3)	W
R _{th,j-a}	Thermal Resistance, Junction to Ambient	100 (Note 3)	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C

Thermal Data

Symbol	Parameter	Max.	Units
R _{th,j-c}	Thermal Resistance, Junction-to-Case, max	25	°C/W
R _{th,j-a}	Thermal Resistance, Junction-to-Ambient, max	62.5*2	

Note:

1. Pulse width limited by maximum junction temperature
2. Duty cycle \leq 1%
3. Surface mounted on 1 in2 copper pad of FR-4 borad, 270°C/W when mounted on minimum copper pad

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Static

Symbol	Test Conditions	Min	Typ.	Max.	Units
BV _{DSS}	V _{GS} = 0 V , I _D = 250μA	30	--	--	V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.5	3	V
I _{DSS}	V _{DS} = 24 V , V _{GS} = 0 V	--	--	1	μA
	V _{DS} = 20 V , V _{GS} = 0 V , T _J = 125°C			10	
I _{GSS}	V _{GS} = ±20 V , V _{DS} = 0	--	--	±100	nA
I _{D(ON)} *1	V _{DS} = 5 V , V _{GS} = 10 V	3.5	--	--	A
R _{DS(ON)} *1	V _{GS} = 10 V , I _D = 3.5 A	--	45	55	mΩ
	V _{GS} = 4.5 V , I _D = 2 A	--	65	85	
G _{FS} *1	V _{DS} = 5 V , I _D = 3.5 A		5		S

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Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
C_{ISS}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	319	--	pF
C_{OSS}	Output Capacitance		--	66	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	53	--	pF
$Q_g^{*1.2}$	Total Gate Charge	$V_{DS} = 10\text{ V}, I_D = 3.5\text{ A},$ $V_{GS} = 4.5\text{ V}$	--	6	--	nC
$Q_{gs}^{*1.2}$	Gate-Source Charge		--	0.8	--	nC
$Q_{gd}^{*1.2}$	Gate-Drain Charge		--	1.8	--	nC
$t_{d(on)}^{*1.2}$		$V_{DS} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_G = 6\Omega$	--	8	--	ns
$t_r^{*1.2}$			--	2.5	--	ns
$t_{d(off)}^{*1.2}$			--	20	--	ns
$t_f^{*1.2}$			--	5	--	ns

Source-Drain Diode						
Symbol	Parameter	Test Conditions	Min	Typ.	Max.	Units
I_S^{*1}			--	--	2	A
I_{SM}^{*3}			--	--	8	
V_{SD}^{*1}		$I_S = I_F, V_{GS} = 0\text{ V}$	--	--	1.2	V

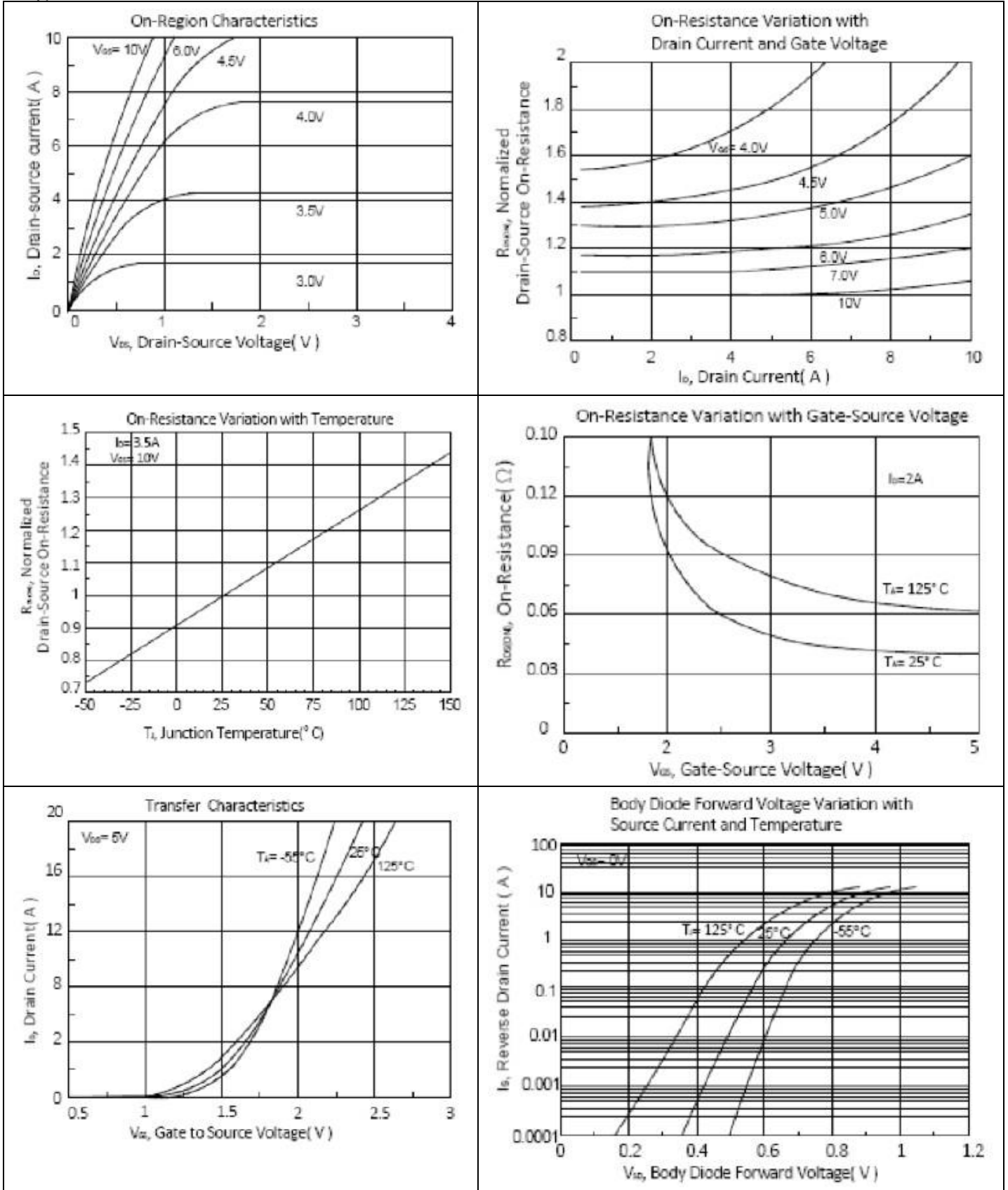
Notes;

1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

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Typical Characteristics



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